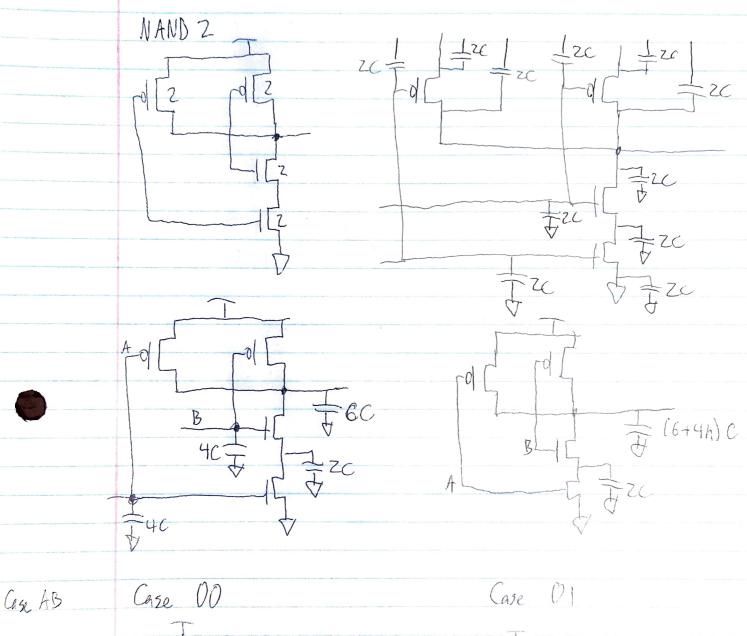


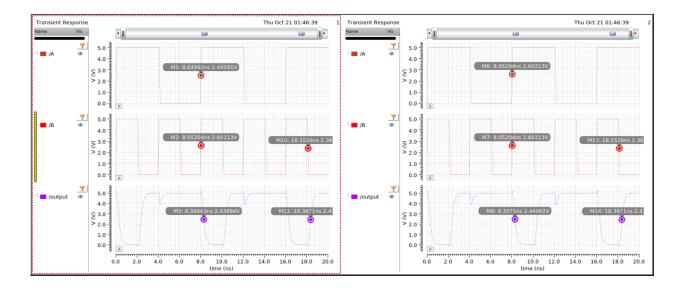
The curves to the right have a higher Bp/Bn ratio than the curves to the left. This feels intuitive because as the width of the pMOS increases, the Beta ratio also increases.

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Case 11

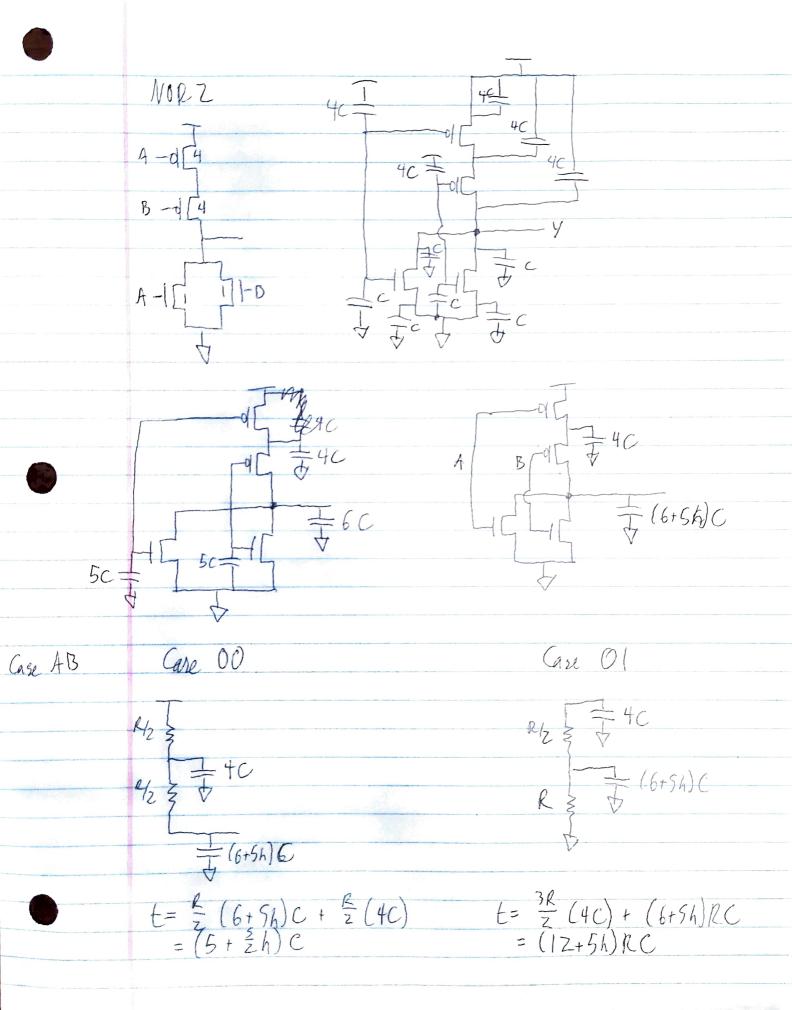
$$t_{pol} = 160 ps$$
 $t_{pol} = 140 ps$ $t_{cdv} = 60 ps$ $t_{pol} = 140 ps$



$$t_{fall} = 255.46 \text{ ps}$$

 $t_{rise} = 234.5 \text{ ps}$

These results do not match up with the by paper results very well, but they do match up enough.



Case 10

R = (6+5h)C

E= (6r5h)RC

tpdr = (5+ = 6)RC tpdf = (12+5h)RC

tcdr=(5+2h)RC tcdf=(3+2h)RC Care I

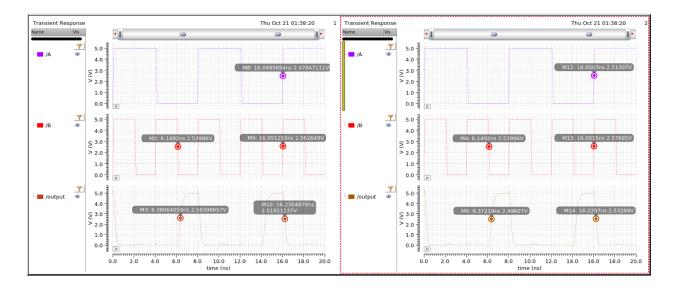
ER ER - (6.5%)C

E=(6+51) C. =

Using h=0, 3/2C=60gs + 1 C= 28gs

toda = 100 ps toda = Wiss

tedr = 100ps tedf = 51ps



$$t_{fall} = 179.25 \text{ ps}$$

 $t_{rise} = 231.44 \text{ ps}$

Again, these values don't match very well to the paper results, however they are close enough for the fact that the paper results are a first degree estimation.

| | NAND | NOR |
|--------------------------|--------|--------|
| t _{pdr} (paper) | 160 ps | 100 ps |
| t _{pdf} (paper) | 140 ps | 240 ps |
| t _{cdr} (paper) | 60 ps | 100 ps |
| t _{cdf} (paper) | 140 ps | 60 ps |
| t _{fall} (sim) | 255 ps | 179 ps |
| t _{rise} (sim) | 234 ps | 231 ps |

My results from paper analysis show much lower delay values than my simulation results, but that is due to the simulation results being more accurate and accounting for more capacitances than is reasonable to do by hand.